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Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KK2700/18	1800	1800	2000
KK2700/20	2000	2000	2100

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	5 mA 80 mA (3)
Critical rate of voltage rise	dv/dt (4)	

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Peak gate power dissipation	P_{GM}		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	I_{GT}		150		mA	V_D=12V;R_L=3ohms;T_j=+25ºC
Gate- trigger voltage	V_{GT}	0.70	2.5		V	V_D=12V;R_L=3ohms;T_j=+25ºC
Peak negative voltage	V_{GRM}		5		V	

Delay time	t_d		3.0	2.5	s	I_{TM}=1000A; V_D=67%V_{DRM} Gate pulse: V_G=30V; R_G=10ohms; t_r=0.1 s; t_p=20 s
Turn-off time (with V_R = -5 V)	t_q		40		s	I_{TM} =2500 A; di/dt =-25 A/ s; V_R =50 V; dv/dt=30V/ s ; V_D= 67%V_{DRM};T_j=125ºC
Reverse recovery charge	Q_{rr}				C	I_{TM}=2500 A;di/dt=-10A/ s; V_R=50 V; T_j=125ºC

Operating temperature	T_j	-40	+125		ºC	
Storage temperature	T_{stg}	-40	+140		ºC	
Thermal resistance - junction to case	$R_{\Theta\ (j\text{-}c)}$		0.01		ºC/W	Double sided cooled
Thermal resistance - case to heatsink	$R_{\Theta\ (c\text{-}s)}$		0.003		ºC/W	Double sided cooled
Mounting force	F	33	37	35	kN